

Data Sheet

March 11, 2008

Low Noise LDO with Low IQ, High PSRR

intercil

ISL9008A is a high performance single low noise, high PSRR LDO that delivers a continuous 150mA of load current. It has a low standby current and is stable with 1μ F of MLCC output capacitance with an ESR of up to $200m\Omega$.

The ISL9008A has a high PSRR of 65dB and output noise less than $45\mu V_{RMS}$. When coupled with a no load quiescent current of $46\mu A$ (typical), and $0.5\mu A$ shutdown current, the ISL9008A is an ideal choice for portable wireless equipment.

The ISL9008A comes in several fixed voltage options with $\pm 1.8\%$ output voltage accuracy over-temperature, line and load. Other output voltage options may be available upon request.

ISL9008A (5 LD SC-70)

TOP VIEW

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vo

VIN

GND

Pinouts

Features

- High performance LDO with 150mA continuous output
- Excellent transient response to large current steps
- Excellent load regulation: <0.1% voltage change across full range of load current
- High PSRR: 65dB @ 1kHz
- Wide input voltage capability: 2.3V to 6.5V
- Very low quiescent current: 46µA
- Low dropout voltage: typically 200mV @ 150mA
- Low output noise: typically 45µV_{RMS} @ 100µA (1.5V)
- Stable with 1µF to 4.7µF ceramic capacitors
- Shutdown pin turns off LDO with 1µA (max) standby current
- Soft-start limits input current surge during enable
- · Current limit and overheat protection
- ±1.8% accuracy over all operating conditions
- 5 Ld SC-70 package or 6 Ld µTDFN package

WWWW 4BOT C. COM20% to +85% operating tengerature ange • Pb-free (RoHS compliant)

Applications

- PDAs, cell phones and smart phones
- Portable instruments, MP3 players
- · Handheld devices including medical handhelds



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Ordering Information

PART NUMBER (Note 4)	PART MARKING	V _O VOLTAGE (V) (Note 1)	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
ISL9008AIENZ-T (Note 2)	CBV	3.3	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIEMZ-T (Note 2)	СВТ	3.0	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIEKZ-T (Note 2)	CBS	2.85	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIEJZ-T (Note 2)	CBR	2.8	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIEHZ-T (Note 2)	СВР	2.75	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIEFZ-T (Note 2)	CBN	2.5	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIETZ-T (Note 2)	CDW	1.9	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIECZ-T (Note 2)	СВМ	1.8	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIEBZ-T (Note 2)	CBL	1.5	-40 to +85	5 Ld SC-70	P5.049
ISL9008AIRUBZ-T (Note 3)	Р	1.5	-40 to +85	6 Ld μTDFN	L6.1.6x1.6A
ISL9008AIRUCZ-T (Note 3)	Q	1.8	-40 to +85	6 Ld μTDFN	L6.1.6x1.6A
ISL9008AIRUFZ-T (Note 3)			-40 to +85		L6.1.6x1.6A
ISL9008AIRUHZ-T		2.75	-40 to +85	οLαμΊθηΝ	L6.1.6x1.6A
ISL9008AIRUJZ-T (Note 3)	Т	2.8	-40 to +85	6 Ld μTDFN	L6.1.6x1.6A
ISL9008AIRUKZ-T (Note 3)	V	2.85	-40 to +85	6 Ld μTDFN	L6.1.6x1.6A
ISL9008AIRUMZ-T (Note 3)	W	3.0	-40 to +85	6 Ld μTDFN	L6.1.6x1.6A
ISL9008AIRUNZ-T (Note 3)	Y	3.3	-40 to +85	6 Ld µTDFN	L6.1.6x1.6A

NOTES:

1. For other output voltages, contact Intersil Marketing.

 These Intersil Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate PLUS ANNEAL - e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

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 e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are
 MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

4. Please refer to TB347 for details on reel specifications.

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Absolute Maximum Ratings

Supply Voltage (VIN)	 +7.1V
V _O Pin	 +3.6V
All Other Pins	 -0.3V to (VIN+0.3V)

Recommended Operating Conditions

Ambient Temperature Range (T _A)	40°C to +85°C
Supply Voltage (V _{IN})	2.3 to 6.5V

Thermal Information

Thermal Resistance	θ _{JA} (°C/W)
5 Ld SC-70 Package (Note 5)	231
6 Ld µTDFN Package (Note 6)	125
Junction Temperature Range40°	C to +125°C
Operating Temperature Range40	°C to +85°C
Storage Temperature Range65°	C to +150°C
Pb-free reflow profilese	e link below
http://www.intersil.com/pbfree/Pb-FreeReflow.asp	

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

- 5. θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details.
- 6. θ_{JA} is measured in free air with the component mounted on a high effective thermal conductivity test board with "direct attach" features. See Tech Brief TB379.

Electrical Specifications	Unless otherwise noted, all parameters are established over the operational supply voltage and temperature
	range of the device as follows:

 $T_A = -40^{\circ}C$ to $+85^{\circ}C$; $V_{IN} = (V_O + 0.5V)$ to 6.5V with a minimum V_{IN} of 2.3V; $C_{IN} = 1\mu$ F; $C_O = 1\mu$ F.

PARAMETER	SYMBOL	. TEST CONDITIONS (ТҮР	MAX (Note 9)	UNITS
DC CHARACTERISTICS					•	
Supply Voltage	V _{IN}		2.3		6.5	V
Ground Current	I _{DD}	Quiescent condition: $I_0 = 0\mu A$		46	66	μΑ
Shutdown Current	I _{DDS}			0.5	1.2	μΑ
UVLO Threshold	V _{UV+}		1.9	2.1	2.3	V
\\\/\\\/\\	V _{UV} D	DTIC com/Into		1.8	2.0	V
Regulation Voltage Acturacy	Y.D	midal a country of $V_{IN} = V_0 + V_5 V_1 = 0 \text{ mA}$, T = -25°C	-07		+0.7	%
		$V_{IN} = V_O + 0.5V$ to 6.5V, $I_O = 10\mu$ A to150mA, $T_J = +25^{\circ}C$	-0.8		+0.8	%
		$V_{IN} = V_O + 0.5V$ to 6.5V, $I_O = 10\mu A$ to 150mA, $T_J = -40^{\circ}C$ to +125°C	-1.8		+1.8	%
Maximum Output Current	I _{MAX}	Continuous	150			mA
Internal Current Limit	I _{LIM}		175	265	355	mA
Drop-out Voltage (Note 8)	V _{DO1}	$I_{O} = 150 \text{mA}; V_{O} < 2.5 \text{V}$		300	500	mV
	V _{DO2}	I_{O} = 150mA; 2.5V \leq V $_{O}$ \leq 2.8V		250	400	mV
	V_{DO3}	I_{O} = 150mA; 2.8V < V_{O}		200	325	mV
Thermal Shutdown	T _{SD+}			140		°C
Temperature	T _{SD-}			110		°C
AC CHARACTERISTICS						
Ripple Rejection (Note 7)		$I_{O} = 10$ mA, $V_{IN} = 2.8V(min), V_{O} = 1.8V$				
		@ 1kHz		65		dB
		@ 10kHz		45		dB
		@ 100kHz		35		dB
Output Noise Voltage (Note 7)		V _O = 1.5V, T _A = +25°C				
		BW = 10Hz to 100kHz, $I_0 = 100\mu A$		45		μV_{RMS}
		BW = 10Hz to 100kHz, $I_0 = 10$ mA		65		μV_{RMS}
DEVICE START-UP CHARACT	ERISTICS					
Device Enable Time	^t EN	Time from assertion of the ENx pin to when the output voltage reaches 95% of the VO(nom)		250	500	μs
LDO Soft-start Ramp Rate	tSSR	Slope of linear portion of LDO output voltage ramp during start-up		30	60	µs/V

Electrical Specifications Unless otherwise noted, all parameters are established over the operational supply voltage and temperature range of the device as follows:

 $T_A = -40^{\circ}C$ to +85°C; $V_{IN} = (V_O + 0.5V)$ to 6.5V with a minimum V_{IN} of 2.3V; $C_{IN} = 1\mu$ F; $C_O = 1\mu$ F. (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	ТҮР	MAX (Note 9)	UNITS
EN PIN CHARACTERISTICS						
Input Low Voltage	VIL		-0.3		0.4	V
Input High Voltage	VIH		1.4		V _{IN} + 0.3	V
Input Leakage Current	I _{IL} , I _{IH}				0.1	μΑ
Pin Capacitance	C _{PIN}	Informative		5		pF

NOTES:

- 7. Limits established by characterization and are not production tested.
- 8. VOx = 0.98*VOx(NOM); Valid for VOx greater than 1.85V.

9. Parts are 100% tested at +25°C. Temperature limits established by characterization and are not production tested.

0.8 $V_{O} = 3.3V$ I_{LOAD} = 0mA 0.6 OUTPUT VOLTAGE, V_O (%) 0.4 +25°C 0.2 0.0 -0.2 -85°C -0.4 -0.6 40°C -0.8 3.8 4.2 5.0 5.4 5.8 6.2 6.6 3.4 4.6 **INPUT VOLTAGE (V)**







FIGURE 3. OUTPUT VOLTAGE vs LOAD CURRENT

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FIGURE 2. OUTPUT VOLTAGE CHANGE (%) vs INPUT VOLTAGE (3.3V OUTPUT)





Typical Performance Curves (Continued)

5 intersil

5.0

4.5

5.5

6.0 6.5

0

1.5

2.0 2.5 3.0

3.5

4.0

INPUT VOLTAGE (V) FIGURE 9. GROUND CURRENT vs INPUT VOLTAGE 175

125

100 LOAD CURRENT (mA) 150

25

50

0

75

FIGURE 10. GROUND CURRENT vs LOAD



Typical Performance Curves (Continued)



80 ТПШ 10mA 70 60 50mA PSRR (dB) 50 40 30 V_{IN} = 3.9V 20 V_O = 1.8V $C_{LOAD} = 1 \mu F$ 10 0.1k 1k 100k 1M 10k FREQUENCY (Hz)

FIGURE 14. LINE TRANSIENT RESPONSE, 2.8V OUTPUT







Typical Performance Curves (Continued)



FIGURE 17. SPECTRAL NOISE DENSITY vs FREQUENCY

Pin Description

5 LD SC-70 PIN NUMBER	6 LD μTDFN PIN NUMBER	PIN NAME	DESCRIPTION
5	1	VO	LDO Output. Connect a 1µF capacitor of value to GND
2	2	GND	GND is the connection to system ground. Connect to PCB Ground plane.
4	3 and 5	NC	No connect.
3			Output Enable. When this signal goes I igh, the LDO is turned on
1	VV VV VV		Sup Iy Voltage/LLO mut. Connect a 1 JF car actor oGND.

Typical Application





Block Diagram



Functional Description

The ISL9008A contains all circuitry required to implement a high performance LDO. High performance is achieved through a circuit that delivers fast transient response to varying load conditions. In a quiescent condition, the ISL9008A adjusts its biasing to achieve the lowest standby current consumption.

thermal shutdown protection, and soft-start. Smart Thermal shutdown protects the device against overheating. Soft-start minimizes start-up input current surges without causing excessive device turn-on time.

Power Control

The ISL9008A has an enable pin, EN, to control power to the LDO output. When EN is low, the device is in shutdown mode. In this condition, all on-chip circuits are off, and the device draws minimum current, typically less than 0.3μ A. When the EN pin goes high, the device first polls the output of the UVLO detector to ensure that VIN voltage is at least 2.1V (typical). Once verified, the device initiates a start-up sequence. During the start-up sequence, trim settings are first read and latched. Then, sequentially, the bandgap, reference voltage and current generation circuitry turn on. Once the references are stable, the LDO powers up.

During operation, whenever the VIN voltage drops below about 1.84V, the ISL9008A immediately disables the LDO output. When VIN rises back above 2.1V (assuming the EN pin is high), the device re-initiates its start-up sequence and LDO operation resumes automatically.

Reference Generation

The reference generation circuitry includes a trimmed bandgap, a trimmed voltage reference divider, a trimmed current reference generator, and an RC noise filter.

The bandgap generates a zero temperature coefficient (TC) voltage for the regulator reference and other voltage references required for current generation and over-ten perature detection. A current generator provides references required for adaptive biasing as well as references for LDO output

adaptive biasing as well as references for LDO output current limit and thermal shutdown determination.

LDO Regulation and Programmable Output Divider

The LDO Regulator is implemented with a high-gain operational amplifier driving a PMOS pass transistor. The design of the ISL9008A provides a regulator that has low quiescent current, fast transient response, and overall stability across all operating and load current conditions. LDO stability is guaranteed for a 1µF to 4.7µF output capacitor that has a tolerance better than 20% and ESR less than 200m Ω . The design is performance-optimized for a 1µF capacitor. Unless limited by the application, use of an output capacitor value above 4.7µF is not recommended as LDO performance improvement is minimal.

Soft-start circuitry integrated into each LDO limits the initial ramp-up rate to about 30µs/V to minimize current surge. The ISL9008A provides short-circuit protection by limiting the output current to about 265mA (typ).

The LDO uses an independently trimmed 1V reference as its input. An internal resistor divider drops the LDO output voltage down to 1V. This is compared to the 1V reference for regulation. The resistor division ratio is programmed in the factory.

Overheat Detection

The bandgap outputs a proportional-to-temperature current that is indicative of the temperature of the silicon. This current is compared with references to determine if the device is in danger of damage due to overheating. When the die temperature reaches about +140°C, the LDO momentarily shuts down until the die cools sufficiently. In the overheat condition, if the LDO sources more than 50mA it will be shut off. Once the die temperature falls back below about +110°C, the disabled LDO is re-enabled and soft-start automatically takes place.

www.BDTIC.com/Intersil

Ultra Thin Dual Flat No-Lead Plastic Package (UTDFN)



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P5.049

Small Outline Transistor Plastic Packages (SC70-5)





WITH PLATING

,		INCHES MILLIMETERS				
ر آ	SYMBOL	MIN	MAX	MIN	MAX	NOTES
	А	0.031	0.043	0.80	1.10	-
	A1	0.000	0.004	0.00	0.10	-
— E1	A2	0.031	0.039	0.80	1.00	-
	b	0.006	0.012	0.15	0.30	-
	b1	0.006	0.010	0.15	0.25	
Ц	С	0.003	0.009	0.08	0.22	6
	c1	0.003	0.009	0.08	0.20	6
→ < C	D	0.073	0.085	1.85	2.15	3
	E	0.071	0.094	1.80	2.40	-
	E1	0.045	0.053	1.15	1.35	3
	е	0.025	6 Ref	0.65	Ref	-
	e1	0.051	2 Ref	1.30	Ref	-
	L	0.010	0.018	0.26	0.46	4
	L1	0.017	7 Ref.	0.420) Ref.	-
	L2	0.006	BSC	0.15	BSC	
	α	0 ⁰	8 ⁰	0 ⁰	8 ⁰	-
	Ν	Ę	5	Ę	5	5
	R	0.004	-	0.10	-	
	MR1	0.004	0.010	Q .15	0.25	
	JHH /					Rev. 3 7/07

5 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE

BASE METAL

b1

1 c1







TYPICAL RECOMMENDED LAND PATTERN

NOTES:

- 1. Dimensioning and tolerances per ASME Y14.5M-1994.
- 2. Package conforms to EIAJ SC70 and JEDEC MO-203AA.
- 3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
- 4. Footlength L measured at reference to gauge plane.
- 5. "N" is the number of terminal positions.
- 6. These Dimensions apply to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
- 7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.